

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-6 (Canceled).

7 (Previously Presented). A light-emitting device comprising:

a display portion formed over a substrate, said display portion comprising a switching element and a current control element; and

a driver circuit comprising an inverter circuit formed over said substrate,

wherein all semiconductor elements in said switching element, said current control element, and said inverter circuit are n-channel type semiconductor elements,

wherein said display portion comprises a plurality of pixels, and

wherein each of said plurality of pixels comprises a light-emitting element.

8 (Previously Presented). A light-emitting device according to claim 7, wherein said substrate is a plastic substrate covered with a protective film.

9 (Original). A light-emitting device according to claim 7, wherein said semiconductor elements comprise thin-film transistors.

10 (Original). A light-emitting device according to claim 7, wherein said driver circuit comprises at least one of an EEMOS circuit and an EDMOS circuit.

11 (Canceled).

12 (Previously Presented). A light-emitting device according to claim 7, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

13 (Previously presented). A light-emitting device comprising:
a display portion comprising a plurality of pixels formed over a substrate; and
a driver circuit formed over said substrate,
wherein said driver circuit comprises a decoder circuit containing a plurality of NAND circuits,
wherein each of the plurality of NAND circuits includes n channel type first, second, third and fourth semiconductor elements,
wherein a signal inputted into third semiconductor element is a signal of an opposite polarity relative to that of a signal inputted into first semiconductor element,
wherein a signal inputted into fourth semiconductor element is a signal of an opposite polarity relative to that of a signal inputted into second semiconductor element, and
wherein each of said plurality of pixels comprises a light-emitting element.

14 (Previously presented). A light-emitting device according to claim 13, wherein third and fourth semiconductor elements are connected in series, and first and second semiconductor elements are connected in parallel.

15 (Previously Presented). A light-emitting device according to claim 13, wherein said substrate is a plastic substrate covered with a protective film.

16 (Previously presented). A light-emitting device according to claim 13, wherein first, second, third, and fourth semiconductor elements comprise thin-film transistors.

17 (Original). A light-emitting device according to claim 13, wherein said light-emitting device is an electro-luminescent display device.

18 (Previously presented). A light-emitting device according to claim 13, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

19 (Previously Presented). A light-emitting device comprising:
a display portion comprising a plurality of pixels formed over a substrate; and
a driver circuit comprising a buffer circuit formed over said substrate,
wherein all semiconductor elements in said buffer circuit are n-channel type semiconductor elements, and
wherein said buffer circuit comprises a first semiconductor element and a second semiconductor element connected in series with said first semiconductor element, and a gate of said second semiconductor element is connected to a drain of said first semiconductor element, and
wherein each of said plurality of pixels comprises a light-emitting element.

20 (Previously Presented). A light-emitting device according to claim 19, wherein said substrate is a plastic substrate covered with a protective film.

21 (Original). A light-emitting device according to claim 19, wherein said semiconductor elements comprise thin-film transistors.

22 (Canceled).

23 (Previously presented). A light-emitting device according to claim 19, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

24 (Previously presented). A light-emitting device comprising:
a display portion comprising a plurality of pixels formed over a substrate; and
a driver circuit comprising a decoder circuit formed over said substrate, said decoder circuit comprising a plurality of NAND circuits and a buffer circuit,

wherein each of the plurality of NAND circuits includes n channel type first, second, third and fourth semiconductor elements,

wherein a signal inputted into third semiconductor element is a signal of an opposite polarity relative to that of a signal inputted into first semiconductor element,

wherein a signal inputted into fourth semiconductor element is a signal of an opposite polarity relative to that of a signal inputted into second semiconductor element,

wherein said buffer circuits comprises a first thin film transistor and a second thin film transistor connected in series with said first thin film transistor, and a gate of said second thin film transistor is connected to a drain of said first thin film transistor, and

wherein each of said pixels comprises a light-emitting element.

25 (Previously Presented). A light-emitting device according to claim 24, wherein said substrate is a plastic substrate covered with a protective film.

26 (Canceled).

27 (Previously presented). A light-emitting device according to claim 24, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

28 (Previously Presented). A light-emitting device comprising:

a display portion comprising a plurality of pixels formed over a substrate; and

a driver circuit formed over said substrate,

wherein said driver circuit comprises a shift register containing a plurality of flip-flop circuits comprising enhancement-type n-channel thin film transistors and depletion-type n-channel thin film transistors,

wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and

wherein each of said plurality of pixels comprises a light-emitting element.

29 (Previously Presented). A light-emitting device according to claim 28, wherein said substrate is a plastic substrate covered with a protective film.

30 (Canceled).

31 (Previously presented). A light-emitting device according to claim 28, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

32 (Previously presented). A light-emitting device comprising:

a display portion comprising a plurality of pixels formed over a substrate; and

a driver circuit formed over said substrate,

wherein said driver circuit comprises a shift register containing a plurality of flip-flop circuits comprising enhancement-type n-channel thin film transistors and depletion-type n-channel thin film transistors, and comprises a plurality of NAND circuits each comprising first and second enhancement-type n-channel thin film transistors and a depletion-type n-channel thin film transistor,

wherein a gate electrode of first enhancement-type n-channel thin film transistor is connected to a first output line,

wherein a source electrode of first enhancement-type n-channel thin film transistor is connected to a ground power supply line,

wherein a drain electrode of first enhancement-type n-channel thin film transistor is connected to second enhancement-type n-channel thin film transistor,

wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and

wherein each of said plurality of pixels comprises a light-emitting element.

33 (Previously Presented). A light-emitting device according to claim 32, wherein said substrate is a plastic substrate covered with a protective film.

34 (Canceled).

35 (Previously presented). A light-emitting device according to claim 32, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

36 (Previously Presented). A light-emitting device comprising:

a display portion comprising a plurality of pixels formed over a substrate; and

a driver circuit formed over said substrate,

wherein each of said plurality of pixels comprises a plurality of enhancement-type n-channel thin film transistors and a plurality of depletion-type n-channel thin film transistors,

wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and

wherein each of said plurality of pixels comprises a light-emitting element.

37 (Previously Presented). A light-emitting device according to claim 36, wherein said substrate is a plastic substrate covered with a protective film.

38-39 (Canceled).

40 (Previously presented). A light-emitting device according to claim 36, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

41 (Previously Presented). A light-emitting device comprising:
a display portion comprising a plurality of pixels formed over a substrate; and
a driver circuit formed over said substrate,
wherein each of said pixels comprises an SRAM formed by a plurality of enhancement-type n-channel thin film transistors and a plurality of depletion-type n-channel thin film transistors,
wherein all semiconductor elements in said display portion and said driver circuit are n-channel type semiconductor elements, and
wherein each of said plurality of pixels comprises a light-emitting element.

42 (Canceled).

43 (Previously Presented). A light-emitting device according to claim 41, wherein said substrate is a plastic substrate covered with a protective film.

44 (Canceled).

45 (Previously Presented). A light-emitting device according to claim 41, wherein said light-emitting device is incorporated in one selected from the group consisting of an EL display, an image playback device, a personal computer, a video camera, a digital camera, a mobile computer, a mobile telephone, and an audio.

46 (Previously Presented). A light-emitting device according to claim 28, wherein each of said plurality of flip-flop circuits comprises an enhancement-type n-channel thin film transistor and two circuits.

47 (Previously Presented). A light-emitting device according to claim 46, wherein one of the circuits is an EEMOS circuit.

48 (Previously Presented). A light-emitting device according to claim 46, wherein one of the circuits is an EDMOS circuit.

49 (Previously Presented). A light-emitting device according to claim 46, wherein each of said plurality of flip-flop circuits further comprises an inverter circuit.

50 (Currently Amended). A light-emitting device according to claim 28, wherein one of the enhancement-type n-channel thin film transistors ~~[[are]]~~ is electrically connected with one of the depletion-type n-channel thin film transistors.

51 (Previously Presented). A light-emitting device according to claim 46, wherein said plurality of flip-flop circuits are connected in series.

52 (Canceled).

53 (Previously presented). A light-emitting device according to claim 7, wherein a semiconductor element in the display portion has at least two channel forming regions.

54 (Previously presented). A light-emitting device according to claim 13, wherein a semiconductor element in the display portion has at least two channel forming regions.

55 (Previously presented). A light-emitting device according to claim 19, wherein a semiconductor element in the display portion has at least two channel forming regions.

56 (Previously presented). A light-emitting device according to claim 24, wherein a semiconductor element in the display portion has at least two channel forming regions.

57 (Previously presented). A light-emitting device according to claim 28, wherein a semiconductor element in the display portion has at least two channel forming regions.

58 (Previously presented). A light-emitting device according to claim 32, wherein a semiconductor element in the display portion has at least two channel forming regions.

59 (Previously presented). A light-emitting device according to claim 36, wherein a semiconductor element in the display portion has at least two channel forming regions.

60 (Previously presented). A light-emitting device according to claim 41, wherein a semiconductor element in the display portion has at least two channel forming regions.

61 (Canceled).

62 (Previously presented). A light-emitting device according to claim 7, wherein each of said plurality of pixels comprises a capacitor.

63 (Previously presented). A light-emitting device according to claim 13, wherein each of said plurality of pixels comprises a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

64 (Previously presented). A light-emitting device according to claim 19, wherein each of said plurality of pixels comprises a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

65 (Previously presented). A light-emitting device according to claim 24, wherein each of

said plurality of pixels comprises a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

66 (Previously presented). A light-emitting device according to claim 28, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

67 (Previously presented). A light-emitting device according to claim 32, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

68 (Previously presented). A light-emitting device according to claim 36, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

69 (Previously presented). A light-emitting device according to claim 41, wherein each of said plurality of pixels comprises two semiconductor elements a switching element, a current control element for controlling an amount of current to the light-emitting element, and a capacitor.

70. (Previously presented). A light-emitting device according to claim 7, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

71. (Previously presented). A light-emitting device according to claim 13, wherein the first, second, third and fourth semiconductor element are inverted stagger thin film transistors including microcrystalline semiconductor films.

72. (Previously presented). A light-emitting device according to claim 19, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

73. (Previously presented). A light-emitting device according to claim 24, wherein the first, second, third and fourth semiconductor element are inverted stagger thin film transistors including microcrystalline semiconductor films.

74. (Previously presented). A light-emitting device according to claim 28, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

75. (Previously presented). A light-emitting device according to claim 32, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

76. (Previously presented). A light-emitting device according to claim 36, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.

77. (Previously presented). A light-emitting device according to claim 41, wherein the semiconductor element is an inverted stagger thin film transistor including a microcrystalline semiconductor film.